Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±12	V
Drain Current (Note 5)	Steady State	T_A = +25°C T_A = +70°C	I_D	7.1 5.7	A
Pulsed Drain Current (Note 6)			I_{DM}	28	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	50	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	— —	— —	±80 ±800	nA	V_{GS} = ±12V, V_{DS} = 0V V_{GS} = ±19V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.62	0.9	1.2	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	24 30 50	30 40 63	mΩ	V_{GS} = 10V, I_D = 7.1A V_{GS} = 4.5V, I_D = 6.4A V_{GS} = 2.5V, I_D = 5.0A
Forward Transconductance	g_{fs}	—	10	—	S	V_{DS} = 5V, I_D = 5.1A
Diode Forward Voltage (Note 7)	V_{SD}	—	0.78	1.16	V	V_{GS} = 0V, I_S = 2.1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	555	—	pF	V_{DS} = 5V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	109	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	82	—	pF	

Notes:
5. Device mounted on 2 oz copper pad layout with $R_{\theta JA}$ = 50°C/W.
6. Pulse width ≤10μS, Duty Cycle ≤1%.
7. Short duration pulse test used to minimize self-heating effect.

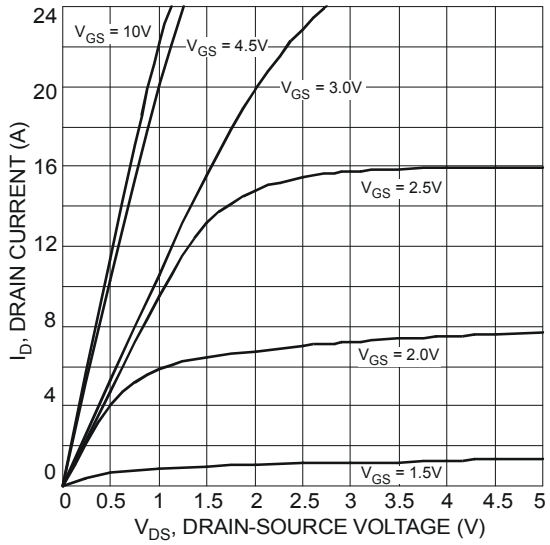


Fig. 1 Typical Output Characteristics

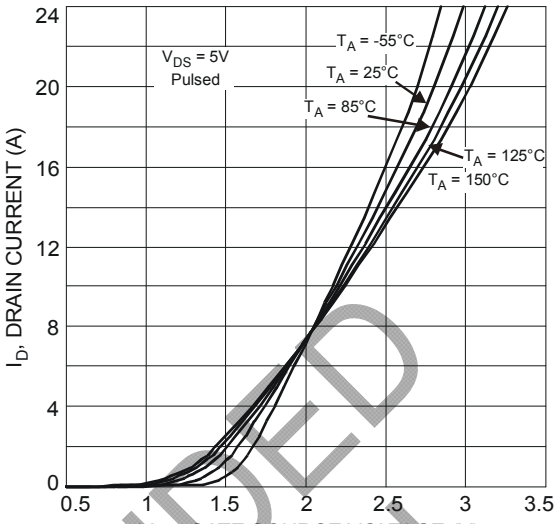


Fig. 2 Typical Transfer Characteristics

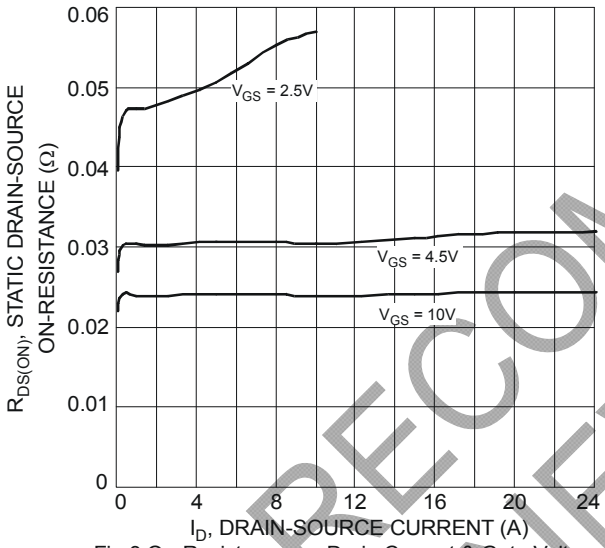


Fig 3 On-Resistance vs. Drain Current & Gate Voltage

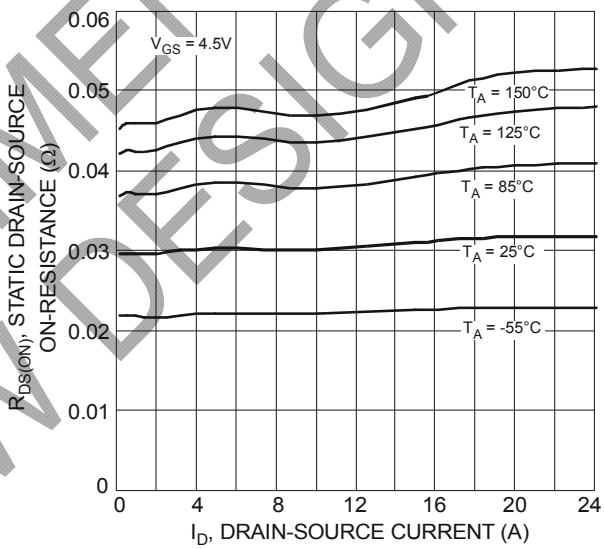


Fig. 4 On-Resistance vs. Drain Current & Temperature

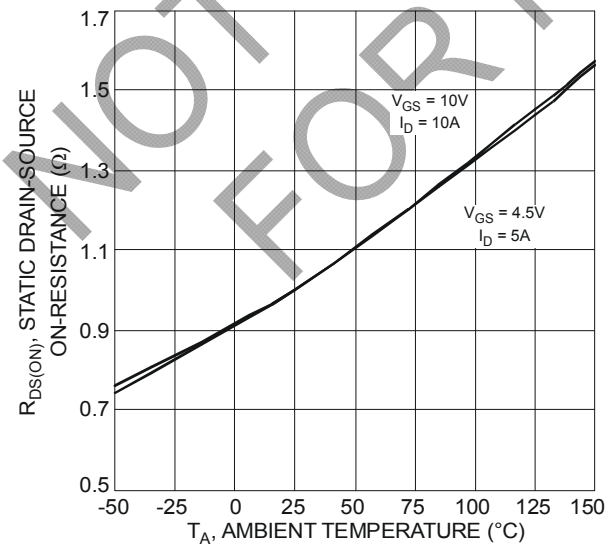


Fig. 5 Static Drain-Source On-Resistance vs. Ambient Temperature

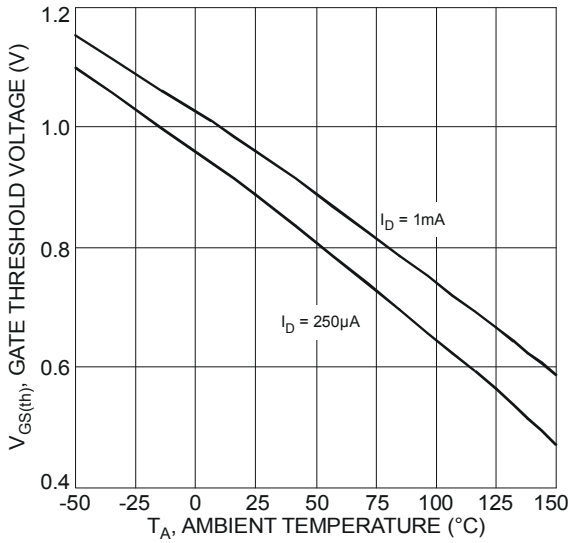


Fig. 6 Gate Threshold Variation vs. Ambient Temperature

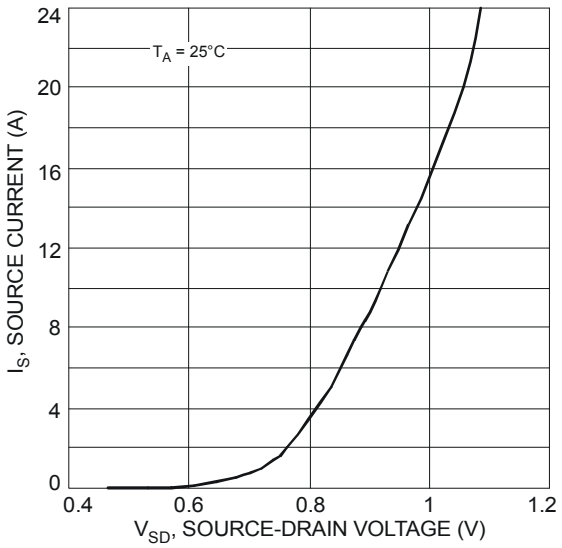


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

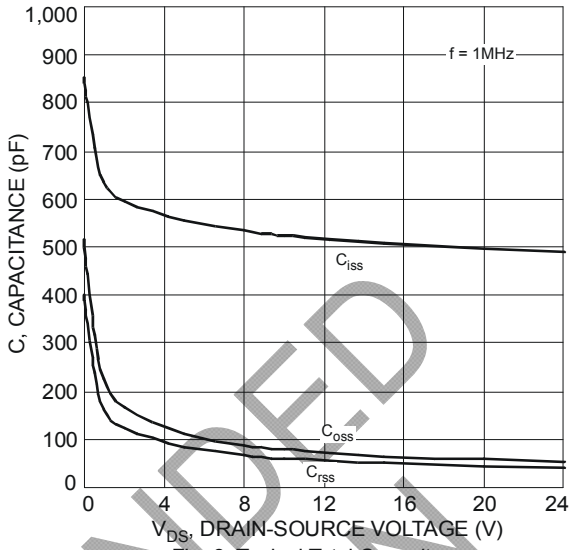


Fig. 8 Typical Total Capacitance

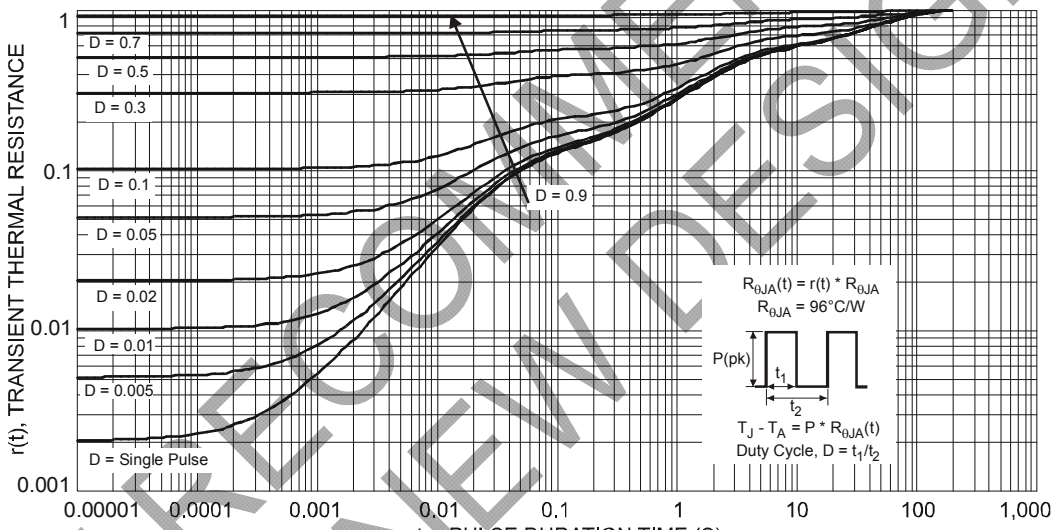
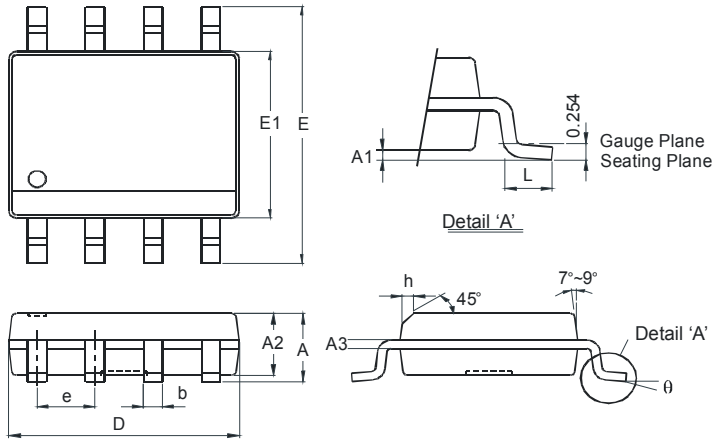


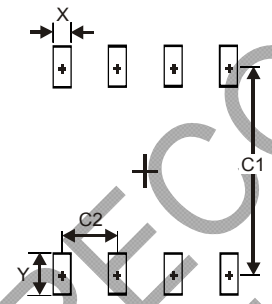
Fig. 9 Transient Thermal Resistance

Package Outline Dimensions



SO-8		
Dim	**Min**	**Max**
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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